

Toru Kanazawa

List of Publications by Year in descending order

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Version: 2024-02-01

13
papers

237
citations

1478505

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1588992

8
g-index

13
all docs

13
docs citations

13
times ranked

434
citing authors

#	ARTICLE	IF	CITATIONS
1	Few-layer HfS ₂ transistors. Scientific Reports, 2016, 6, 22277.	3.3	131
2	High drain current (>2A/mm) InGaAs channel MOSFET at V_D/I_D=0.5V with shrinkage of channel length by InP anisotropic etching. , 2011, , .		30
3	Metamaterial Waveguide Devices for Integrated Optics. Materials, 2017, 10, 1037.	2.9	22
4	Permeability-controlled optical modulator with Tri-gate metamaterial: control of permeability on InP-based photonic integration platform. Scientific Reports, 2015, 5, 8985.	3.3	11
5	Optical Lattice Model Toward Nonreciprocal Invisibility Cloaking. IEEE Journal of Quantum Electronics, 2015, 51, 1-10.	1.9	9
6	Effect of increasing gate capacitance on the performance of a p-MoS₂/HfS₂ van der Waals heterostructure tunneling field-effect transistor. Japanese Journal of Applied Physics, 2019, 58, SBBH02.	1.5	9
7	Vacuum Annealing and Passivation of HfS₂ FET for Mitigation of Atmospheric Degradation. IEICE Transactions on Electronics, 2017, E100.C, 453-457.	0.6	8
8	Sub-50-nm InGaAs MOSFET with n-InP source on Si substrate. , 2013, , .		7
9	Type-II HfS₂/MoS₂ Heterojunction Transistors. IEICE Transactions on Electronics, 2018, E101.C, 338-342.	0.6	6
10	Submicron InP/InGaAs composite channel MOSFETs with selectively regrown N⁺-source/drain buried in channel undercut. , 2010, , .		2
11	Channel thickness dependence on InGaAs MOSFET with n-InP source for high current density. IEICE Electronics Express, 2014, 11, 20140567-20140567.	0.8	2
12	Fabrication of InP/InGaAs channel MOSFET with MOVPE selectively regrown source. , 2009, , .		0
13	Submicron-channel InGaAs MISFET with epitaxially grown source. , 2010, , .		0